

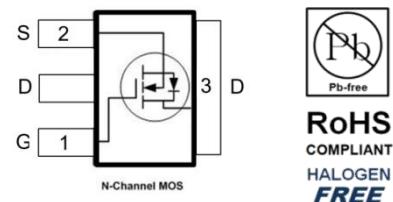
N-Channel 80V MOSFET

E080N8P7AH1

V _{DS} (V)	R _{DS(on),max} (mΩ)	I _D (A)
80V	8.7 @ V _{GS} = 10V	81

Features

- Low R_{DS(on)} trench technology
- Low thermal impedance
- Fast switching speed
- 100% avalanche tested



Applications

- DC/DC conversion
- Power switch
- PD charger
- Moto driver

Package And Ordering Information

Ordering code	Package	Marking
E080N8P7AH1	TO-220	E080N8P7AH1

Ordering Information

Package	Units/ Tube	Tubes/ Inner Box	Units/ Inner Box
TO-220	50	20	1000

Key Performance Parameters

Parameter	Value	Unit
VDS, min @ Tj(max)	80	V
ID, pulse	324	A
RDS(ON), max @ VGS=10V	8.7	mΩ
Qg	112	nC

Absolute Maximum Ratings at Tj=25°C Unless Otherwise Noted

Parameter	Symbol	Limit	Unit
Drain-source voltage	V _{DS}	80	V
Gate-source voltage	V _{GS}	±20	
Continuous drain current	I _D	81	A
		51	
Pulsed drain current	I _{D,pulse}	324	A
Avalanche energy, single pulse	E _{AS}	361	
Power dissipation	P _D	125	W
		50	
Operating junction and storage temperature range	T _J , T _{stg}	-55 To 150	°C

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal resistance, junction-to-case	R _{θJC}	1	°C/W
Thermal resistance, junction-to-ambient	R _{θJA}	-	

Electrical Characteristics at Tj=25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Static						
Drain to source breakdown voltage	V _{(BR)DSS}	80			V	V _{GS} = 0, I _D = 250 μA
Gate-source threshold voltage	V _{GS(th)}	2	2.85	4	V	V _{DS} = V _{GS} , I _D = 250 μA
Gate-body leakage	I _{GSS}			±100	nA	V _{DS} = 0 V, V _{GS} = ±20 V
Zero gate voltage drain current	I _{DSS}			1	μA	V _{DS} = 80 V, V _{GS} = 0 V
Drain-source on-resistance	R _{DS(on)}		7.6	8.7	mΩ	V _{GS} = 10 V, I _D = 40 A
Forward transconductance	g _{fs}		36		S	V _{DS} = 10 V, I _D = 40 A
Gate resistance	R _g		0.5		Ω	f=1MHz

Gate Charge					
Total gate charge	Qg		112		nC $V_{DS} = 40\text{ V}$, $I_D = 20\text{ A}$, $V_{GS} = 10\text{ V}$
Gate-source charge	Qgs		15		
Gate-drain charge	Qgd		45		
Dynamic					
Turn-on delay time	$t_{d(on)}$		30		ns $V_{DS} = 40\text{ V}$, $V_{GS} = 10\text{ V}$, $R_L = 2\Omega$, $R_{GEN} = 6\Omega$
Rise time	t_r		18		
Turn-off delay time	$t_{d(off)}$		65		
Fall time	t_f		30		
Input capacitance	C_{iss}		4450		pF $V_{DS} = 40\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1.0\text{MHz}$
Output capacitance	C_{oss}		210		
Reverse transfer capacitance	C_{rss}		180		
Body Diode					
Diode forward voltage	V_{SD}			1.2	V $V_{GS} = 0\text{ V}$, $I_F = 20\text{ A}$
Reverse recovery time	t_{rr}		7		ns $I_S = 20\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}		40		

Electrical Characteristics Diagrams

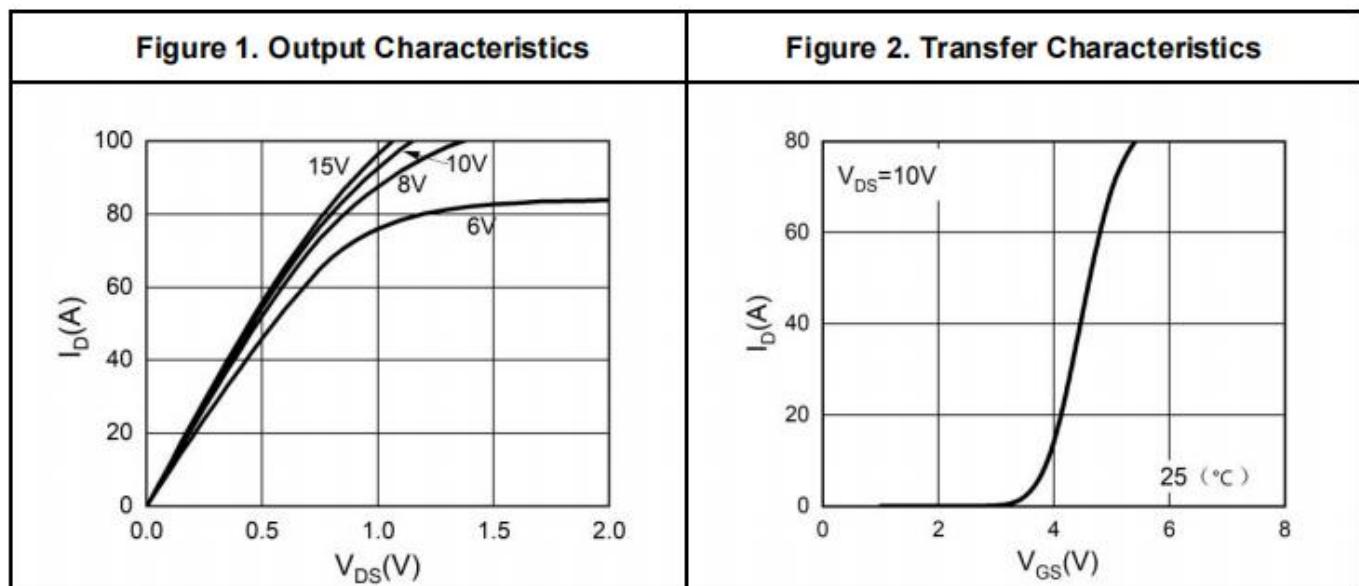


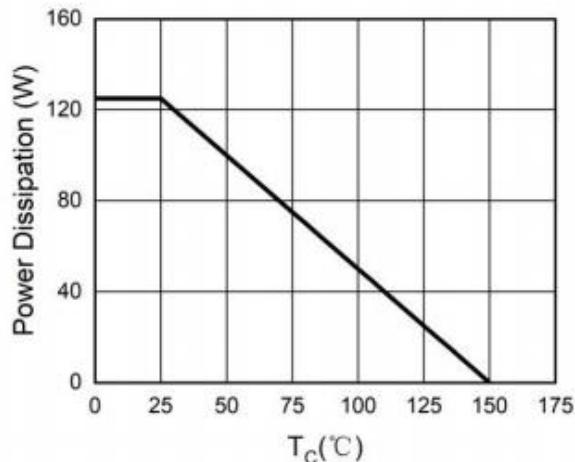
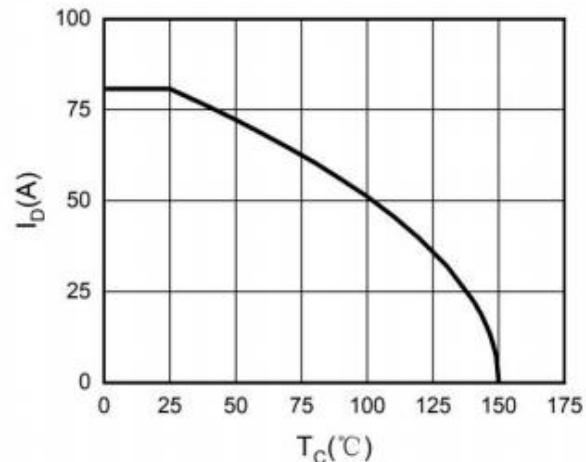
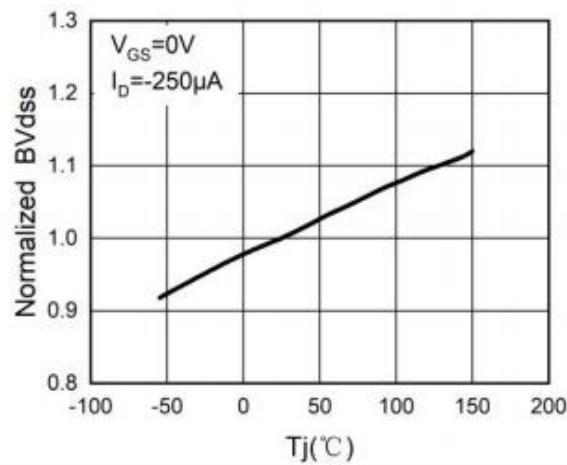
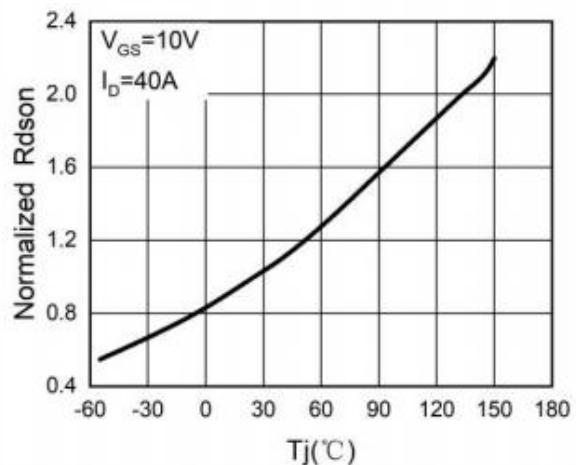
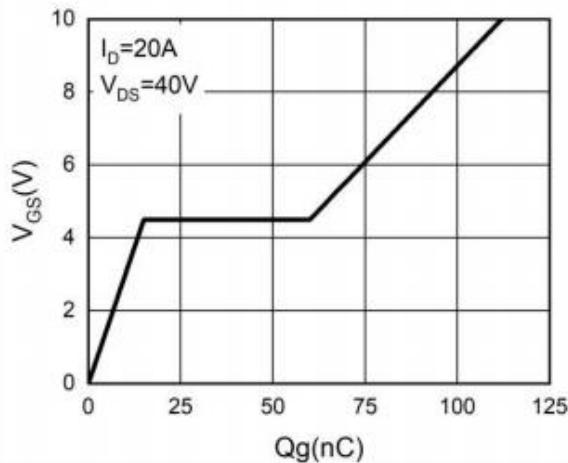
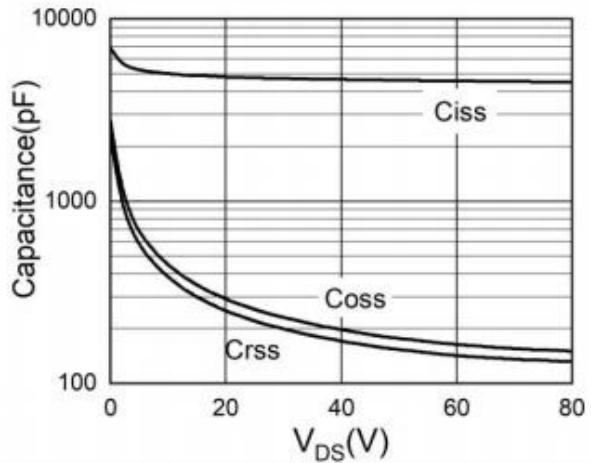
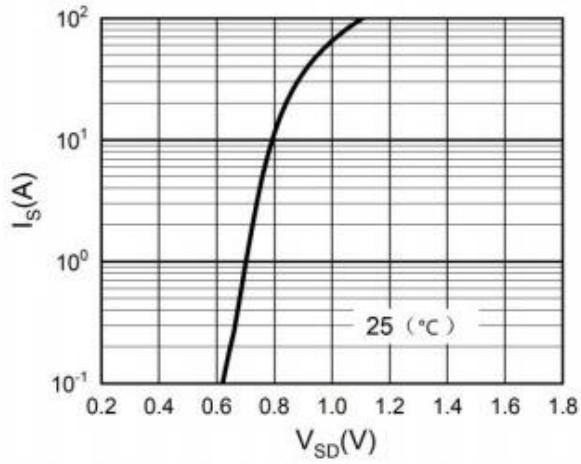
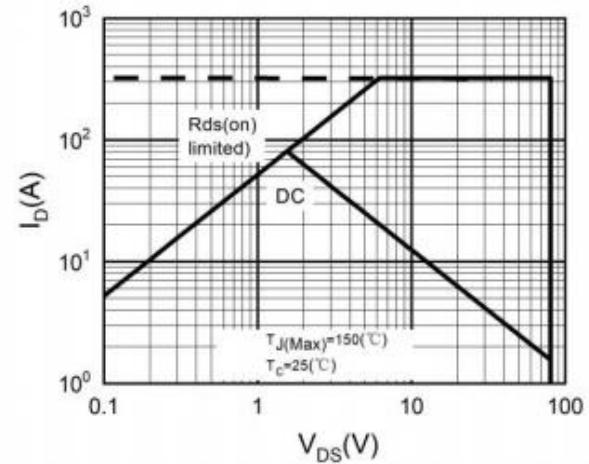
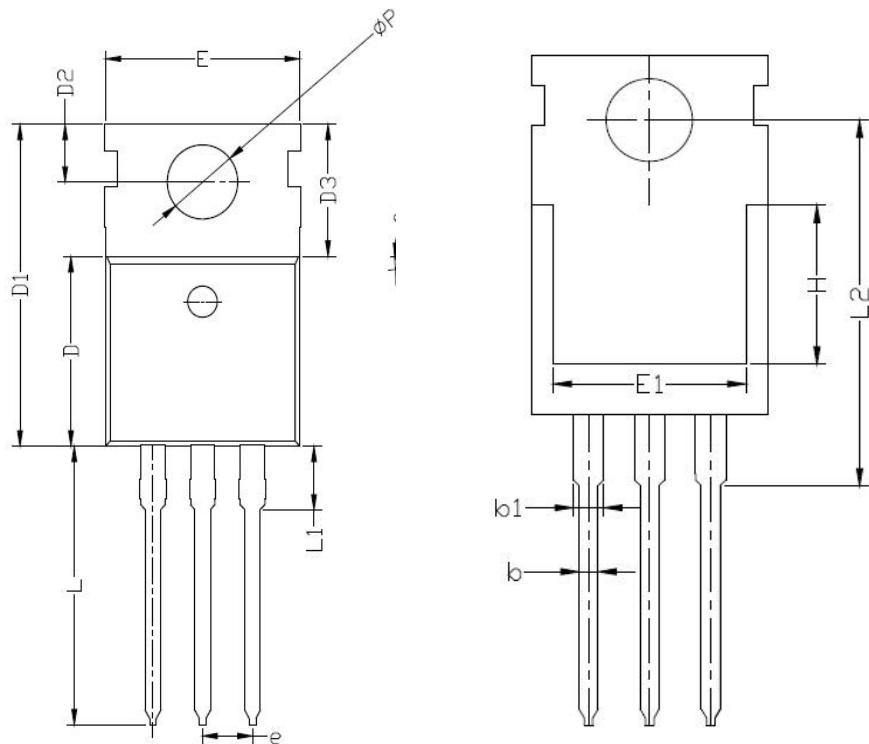
Figure 3. Power Dissipation**Figure 4. Drain Current****Figure 5. BV_{DSS} vs Junction Temperature****Figure 6. $R_{DS(ON)}$ vs Junction Temperature**

Figure 7. Gate Charge Waveforms**Figure 8. Capacitance****Figure 9. Body-Diode Characteristics****Figure 10. Maximum Safe Operating Area**

Package Outline Dimensions


Symbols	Millimeters		
	MIN.	NOM.	MAX.
A	4.27	4.57	4.87
A1	1.15	1.30	1.45
A2	2.20	2.40	2.60
C	0.40	0.50	0.65
L1	2.80	3.10	3.40
L	13.20	13.50	13.70
L2	15.50	15.90	16.30
D	9.00	9.20	9.40
D1	15.10	15.60	16.10
D2	2.60	2.80	3.00
D3	6.20	6.40	6.60
e	2.54 BSC.		
H	6.70	6.90	7.10
E	9.70	9.90	10.10
E1	7.80	8.00	8.20
φP	3.40	3.60	3.80
b	0.70	0.80	0.90
b1	1.17	1.27	1.37
θ	4°	7°	10°
θ1	0°	3°	6°

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